

**Sensitive Gate
Silicon Controlled Rectifiers
Reverse Blocking Thyristors**

**SCRs
8 AMPERES RMS
600 thru VOLTS**

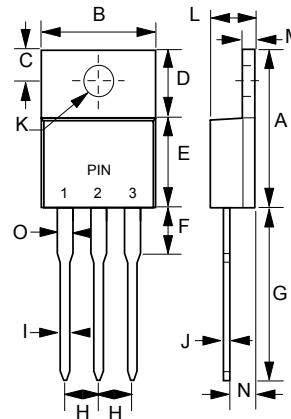
FEATURES

- Blocking Voltage to 600 Volts
- On-State Current Rating of 8 Amperes RMS at 80°C
- High Surge Current Capability - 80 Amperes
- Rugged, Economical TO220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to dv/dt - 5 V/msec Minimum at 110°C
- Pb-Free Package

MECHANICAL DATA

- Case: Molded plastic
- Weight: 0.07 ounces, 2.0 grams

TO-220AB



TO-220AB		
DIM.	MIN.	MAX.
A	14.22	15.88
B	9.65	10.67
C	2.54	3.43
D	5.84	6.86
E	8.26	9.28
F	-	6.35
G	12.70	14.73
H	2.29	2.79
I	0.51	1.14
J	0.40	0.67
K	3.53 \varnothing	4.09 \varnothing
L	3.56	4.83
M	1.14	1.40
N	2.03	2.92
O	1.17	1.37

All Dimensions in millimeter

PIN ASSIGNMENT	
1	Cathode
2	Anode
3	Gate
4	Anode

MAXIMUM RATINGS ($T_j = 25^\circ\text{C}$ unless otherwise noticed)

Rating	Symbol	Value	Unit
Peak Repetitive Off- State Voltage ($T_j = -40$ to 125°C , Sine Wave, 50 to 60 Hz; Gate Open)	V_{DRM} , V_{RRM}	600	Volts
On-State RMS Current (180° Conduction Angles, $T_c = 80^\circ\text{C}$)	$I_{T(RMS)}$	8	Amp
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, $T_j = 25^\circ\text{C}$)	I_{TSM}	80	Amp
Circuit Fusing Consideration ($t = 8.3$ ms)	$I^2 t$	26.5	$\text{A}^2 \text{s}$
Forward Peak Gate Power (Pulse Width ≤ 1.0 μs , $T_c = 80^\circ\text{C}$)	P_{GM}	5.0	Watt
Forward Average Gate Power ($t = 8.3$ ms, $T_c = 80^\circ\text{C}$)	$P_{G(AV)}$	0.5	Watt
Forward Peak Gate Current (Pulse Width ≤ 1.0 μs , $T_c = 80^\circ\text{C}$)	I_{GM}	2.0	Amp
Operating Junction Temperature Range	T_j	-40 to +110	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$

Notice: (1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded

REV. 8, Oct-20010, KTXC09

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance - Junction to Case - Junction to Ambient	RthJC RthJA	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

ELECTRICAL CHARACTERISTICS (T_J=25 °C unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Forward or Reverse Blocking Current (V _D =Rated V _{DRM} and V _{RRM} ; R _{GK} =1K Ohms)	T _J =25°C T _J =110°C	IDRM IRRM	----	----	10 500	µA
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ON CHARACTERISTICS

Peak Forward On-State Voltage (I _{TM} = 16A Peak @T _p ≤2.0 ms, Duty Cycle ≤ 2%)	V _{TM}	----	----	1.8	Volts
Gate Trigger Current (V _D = 12 V; R _L = 100 Ohms)	I _{GT}	5.0	25	200	µA
Holding Current (V _D = 12 V, Gate Open, Initiating Current = 200 mA)	I _H	----	0.5	6.0	mA
Latch Current (V _D = 12 V, I _G = 200 µA)	I _L	----	0.6	8.0	mA
Gate Trigger Voltage (V _D = 12 V; R _L =100 Ohms)	V _{GT}	0.3	0.65	1.0	Volts
Gate Non Trigger Voltage (V _D = 12 V; R _L =100 Ohms), T _J =110°C	V _{GD}	0.2	----	----	Volts

DYNAMIC CHARACTERISTICS

Critical Rate of Rise of Off-State Voltage (V _D =67% V _{DRM} , R _{GK} =1K Ohm, C _{GK} = 1 µF, T _J =110°C)	dv/dt	5.0	15	----	V/µs
Repetitive Critical Rate of Rise of On-State Current I _{PK} =50A, P _w =40 µsec, di _G /dt=1A/µs, I _{gt} =10mA	di/dt	----	----	100	A/µs

*Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I_H	Holding Current

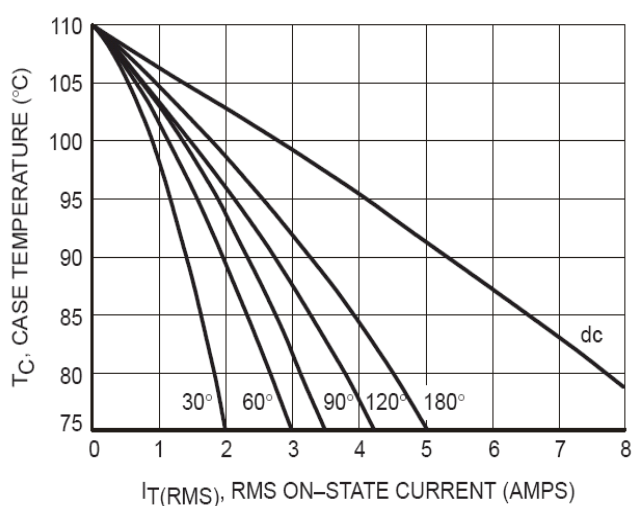
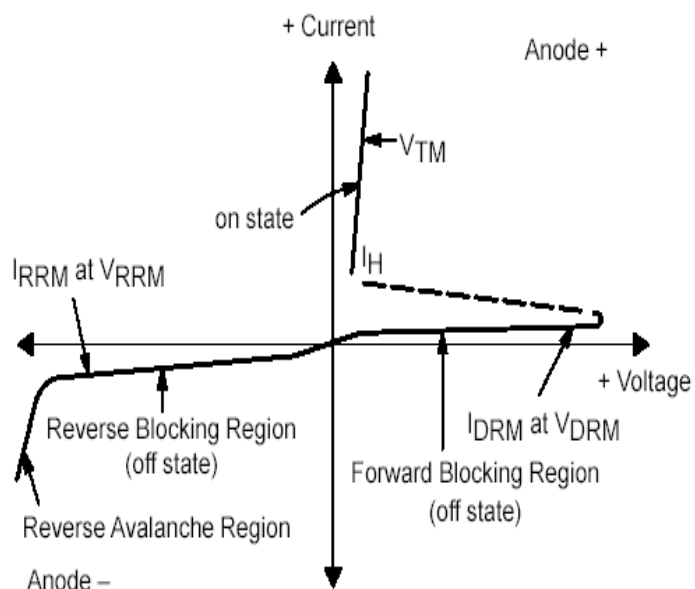


Figure 1. Typical RMS Current Derating

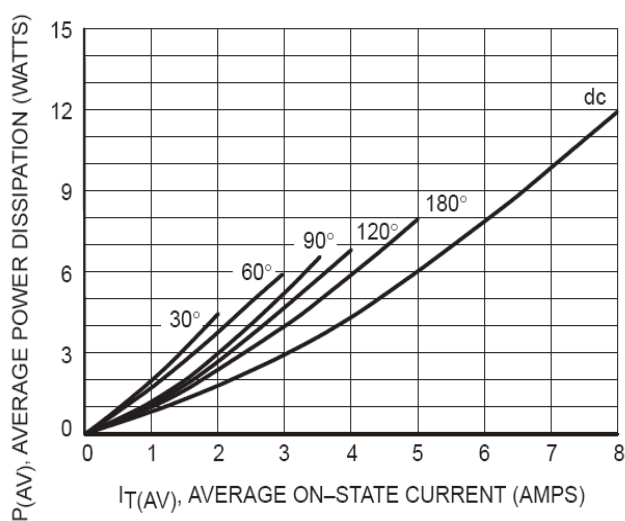


Figure 2. On-State Power Dissipation

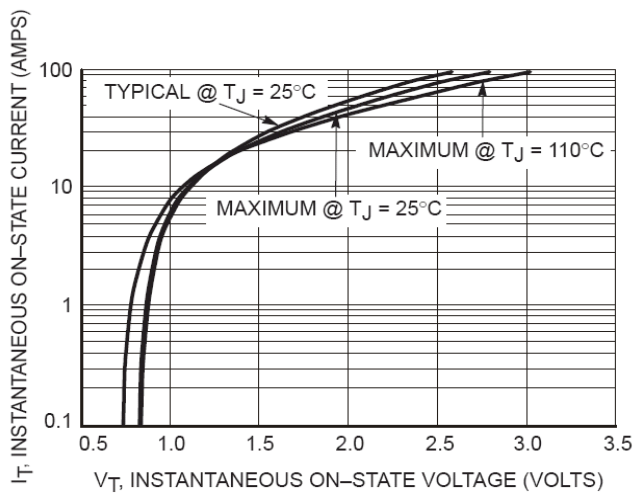


Figure 3. Typical On-State Characteristics

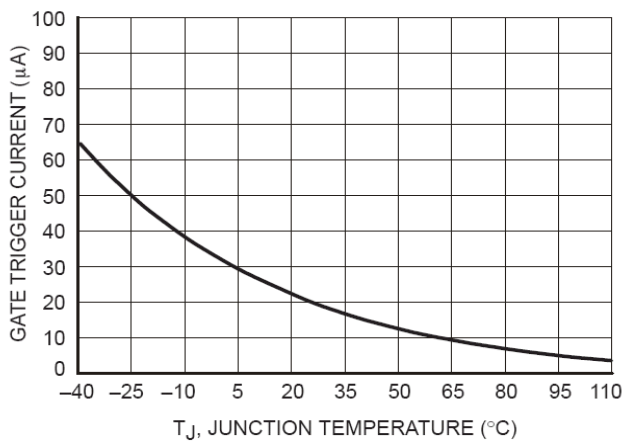


Figure 4. Typical Gate Trigger Current versus Junction Temperature

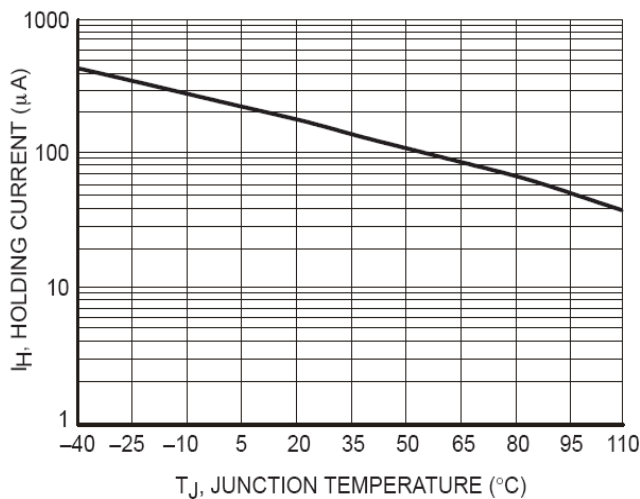


Figure 5. Typical Holding Current versus Junction Temperature

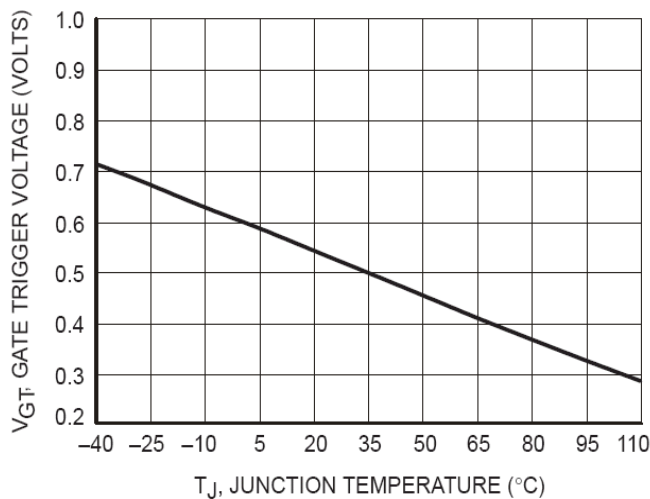


Figure 6. Typical Gate Trigger Voltage versus Junction Temperature

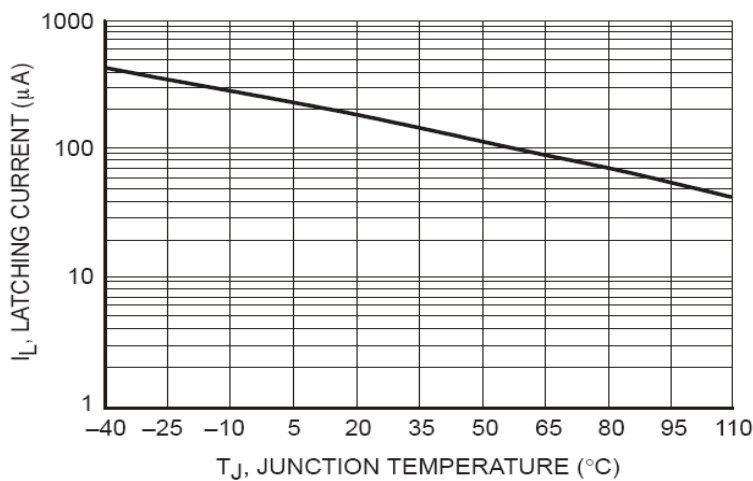


Figure 7. Typical Latching Current versus Junction Temperature

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